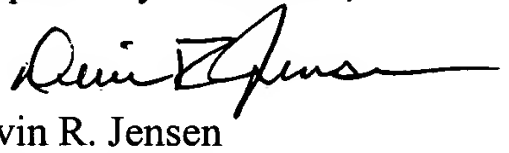
REMARKS

No new matter has been added. The Applicant requests entry of the amendments as set forth in the attachment hereto prior to examination of the application on the merits.

Information Disclosure Statement

Applicant is submitting an Information Disclosure Statement with this Preliminary Amendment and the accompanying CPA and respectfully requests consideration of the included references.

Respectfully Submitted,



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Date: March 14, 2002
DRJ/ps:dh
Enclosure: Version With Markings to Show Changes Made

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

1. (Five Times Amended) A contact for a semiconductor device, comprising:

a single contact plug extending through a first barrier layer planarized down to a transistor gate member, said single contact plug in electrical communication with an active region on a semiconductor substrate;

an individual contact land disposed atop said single contact plug and a portion of said first barrier layer, wherein said contact land is wider than said single contact plug and is substantially planar;

an upper contact extending through a second barrier layer, said second barrier layer disposed over said first barrier layer, to form an electrical contact with said individual contact land.

3. (Five Times Amended) A transistor for the dissipation of electrostatic discharges, comprising:

an intermediate structure comprising a substrate having at least one thick field oxide area, and at least one active area including at least one implanted drain region, and at least one implanted source region, said intermediate structure further including at least one transistor gate member spanned between said at least one drain region and said at least one source region on said at least one active area;

a first barrier layer planarized down to said at least one transistor gate member and substantially covering said at least one field oxide area, said at least one active area, and adjacent said at least one transistor gate member;

at least one drain contact plug extending through said first barrier layer, wherein said at least one drain contact plug is in electrical communication with said at least one drain region on said semiconductor substrate;

at least one source contact plug extending through said first barrier layer, wherein said at least one source contact plug is in electrical communication with said at least one source region on said semiconductor substrate;

an individual drain contact land disposed atop each of said at least one drain contact plugs and a portion of said first barrier layer, said individual drain contact land wider than said at least one drain contact plug and substantially planar;

an individual source contact land disposed atop each of said at least one source contact plugs and a portion of said first barrier layer, said individual source contact land wider than said at least one source contact plug and substantially planar;

a second barrier layer disposed over said first barrier layer, said individual drain contact land, and said individual source contact land;

at least one upper source contact extending through said second barrier layer, said at least one upper source contact is in electrical communication with at least one of said individual source contact lands; and

at least one upper drain contact extending through said second barrier layer, said at least one upper drain contact in electrical communication with at least one of said individual drain contact lands.

19. (Five Times Amended) A semiconductor device including at least one contact, comprising:

a single contact plug extending through a first barrier layer <u>planarized down to a transistor gate member</u>, said single contact plug in electrical communication with an active region on a semiconductor substrate;

an individual contact land disposed atop said single contact plug and a portion of said first barrier layer, said individual contact land wider than said single contact plug and substantially planar; and

an upper contact extending through a second barrier layer, said second barrier layer disposed over said first barrier layer, to form an electrical contact with said individual contact land.

21. (Five Times Amended) A semiconductor device including at least one transistor for the dissipation of electrostatic discharges, comprising:

an intermediate structure comprising a semiconductor substrate having at least one thick field oxide area, and at least one active area including at least one implanted drain region, and at least one implanted source region, said intermediate structure further including at least one transistor gate member spanned between said at least one implanted drain region and said at least one implanted source region on said at least one active area;

a first barrier layer planarized down to said at least one transistor gate member and substantially covering said at least one thick field oxide area, said at least one active area, and adjacent said at least one transistor gate member;

at least one drain contact plug extending through said first barrier layer, wherein said at least one drain contact plug is in electrical communication with said at least one implanted drain region on said semiconductor substrate;

at least one source contact plug extending through said first barrier layer, wherein said at least one source contact plug is in electrical communication with said at least one implanted source region on said semiconductor substrate;

an individual drain contact land disposed atop said at least one drain contact plug and a portion of said first barrier layer, said individual drain contact land wider than said at least one drain contact plug;

an individual source contact land disposed atop said at least one source contact plug and a portion of said first barrier layer, said individual source contact land is wider than said at least one source contact plug;

a second barrier layer disposed over said first barrier layer;

at least one upper source contact extending through said second barrier layer, said at least one upper source contact in electrical communication with at least one said individual source contact land; and

at least one upper drain contact extending through said second barrier layer, said at least one upper drain contact in electrical communication with at least one said individual drain contact land.